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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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# SMD Schottky Barrier Diode



SMD Diodes Specialist

## CDBF54 (RoHs Device)

$I_o = 200 \text{ mA}$   
 $V_R = 30 \text{ Volts}$

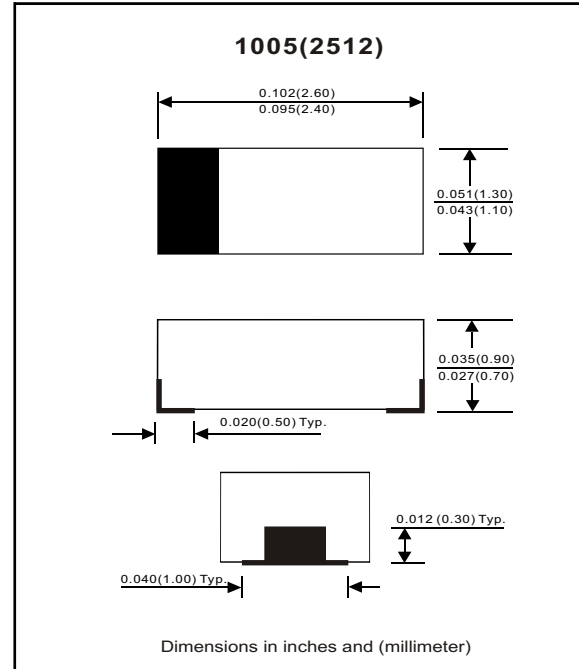


### Features

- Low forward Voltage.
- Designed for mounting on small surface.
- Extremely thin / leadless package.
- Majority carrier conduction.

### Mechanical data

- Case: 1005(2512) standard package, molded plastic.
- Terminals: Gold plated, solderable per MIL-STD-750, method 2026.
- Polarity: Indicated by cathode band.
- Mounting position: Any
- Weight: 0.006 gram(approx.).



### Maximum Rating (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Peak reverse voltage		$V_{RM}$			30	V
Reverse voltage		$V_R$			30	V
RMS reverse voltage		$V_{R(RMS)}$			21	V
Average forward rectified current		$I_o$			200	mA
Repetitive peak forward current		$I_{FRM}$			0.3	A
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	$I_{FSM}$			0.6	A
Power dissipation		$P_D$			200	mW
Storage temperature		$T_{STG}$	-65		+125	$^\circ\text{C}$
Junction temperature		$T_j$			+125	$^\circ\text{C}$

### Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 0.1\text{mA}$ $I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 30\text{mA}$ $I_F = 100\text{mA}$	$V_F$			0.24 0.32 0.4 0.5 1	V
Reverse current	$V_R = 25\text{V}$	$I_R$			2	$\mu\text{A}$
Capacitance between terminals	$f = 1 \text{ MHz}$ , and 1 VDC reverse voltage	$C_T$			10	pF
Reverse recovery time	$I_F=I_R=10\text{mA}$ , $I_{rr}=0.1 \times I_R$ , $R_L=100 \text{ Ohm}$	$T_{rr}$			5	nS

## RATING AND CHARACTERISTIC CURVES (CDBF54)

Fig. 1 - Forward characteristics

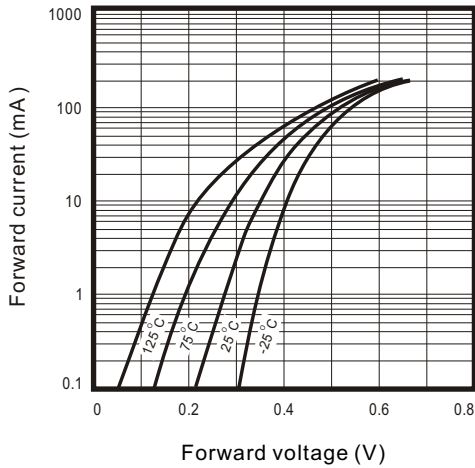


Fig. 2 - Reverse characteristics

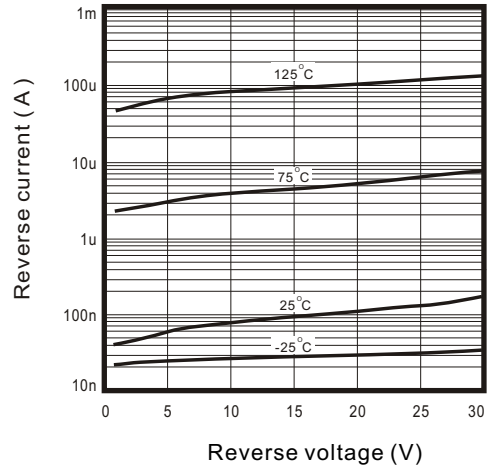


Fig.3 - Capacitance between terminals characteristics

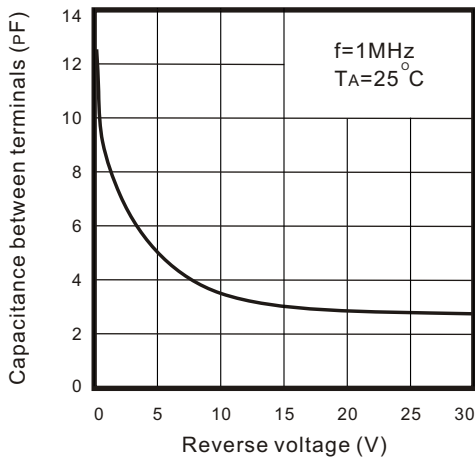


Fig.4 - Current derating curve

